NVJD5121N

Power MOSFET

60 V, 300 mA, Dual N−Channel with ESD Protection, SC−88

Features

- Low $R_{DS(on)}$
- Low Gate Threshold
- Low Input Capacitance
- ESD Protected Gate
- NVJD Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- This is a Pb−Free Device

Applications

- Low Side Load Switch
- DC−DC Converters (Buck and Boost Circuits)

MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	60	V
Gate−to−Source Voltage			V_{GS}	±20	V
Continuous Drain Current (Note 1)	Steady State	T_A = 25°C	I_D	300	mA
		T_A = 85°C		233	
	t ≤ 5 s	T_A = 25°C		310	
		T_A = 85°C		240	
Power Dissipation (Note 1)	Steady State	T_A = 25°C	P_D	300	mW
	t ≤ 5 s			319	
Pulsed Drain Current	t_p = 10 μs		I_{DM}	1200	mA
Operating Junction and Storage Temperature			T_J, T_{STG}	−55 to 175	°C
Source Current (Body Diode)			I_S	250	mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	°C
Gate−Source ESD Rating (HBM)			ESD_{HBM}	2000	V
Gate−Source ESD Rating (MM)			ESD_{MM}	200	V

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit
Junction−to−Ambient – Steady State	$R_{\theta JA}$	500	°C/W
Junction−to−Ambient – t ≤ 5 s	$R_{\theta JA}$	470	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).

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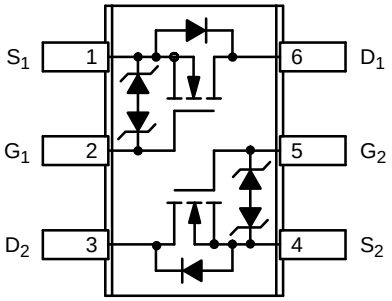
$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D Max
60 V	1.6 Ω @ 10 V	300 mA
	2.5 Ω @ 4.5 V	

SC−88 (SOT−363)

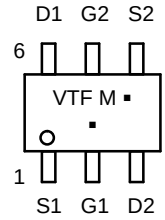


Top View

MARKING DIAGRAM & PIN ASSIGNMENT

1

SC−88/SOT−363
CASE 419B
STYLE 26



VTF = Device Code
M = Date Code
▪ = Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
NVJD5121NT1G	SC−88 (Pb−Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise stated)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 μA		60			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	I_D = 250 μA, ref to 25°C			92		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = 60 V	T_J = 25°C			1.0	μA
			T_J = 125°C			500	
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V				±10	μA
ON CHARACTERISTICS (Note 2)							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = 250 μA		1.0	1.7	2.5	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$				4.0		mV/°C
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 500 mA			1.0	1.6	Ω
		V_{GS} = 4.5 V, I_D = 200 mA			1.2	2.5	
Forward Transconductance	g_{FS}	V_{DS} = 5 V, I_D = 200 mA			80		S
Gate Resistance	R_G				536		Ω
CHARGES AND CAPACITANCES							
Input Capacitance	C_{ISS}	V_{GS} = 0 V, f = 1.0 MHz, V_{DS} = 20 V			26		pF
Output Capacitance	C_{OSS}				4.4		
Reverse Transfer Capacitance	C_{RSS}				2.5		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 4.5 V, V_{DS} = 25 V, I_D = 200 mA			0.9		nC
Threshold Gate Charge	$Q_{G(TH)}$				0.2		
Gate−to−Source Charge	Q_{GS}				0.3		
Gate−to−Drain Charge	Q_{GD}				0.28		
SWITCHING CHARACTERISTICS (Note 3)							
Turn−On Delay Time	$t_{d(on)}$	V_{GS} = 4.5 V, V_{DD} = 25 V, I_D = 200 mA, R_G = 25 Ω			22		ns
Rise Time	t_r				34		
Turn−Off Delay Time	$t_{d(off)}$				34		
Fall Time	t_f				32		
DRAIN−SOURCE DIODE CHARACTERISTICS							
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = 200 mA	T_J = 25°C		0.8	1.2	V
			T_J = 85°C		0.7		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
3. Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES

(T_J = 25°C unless otherwise noted)

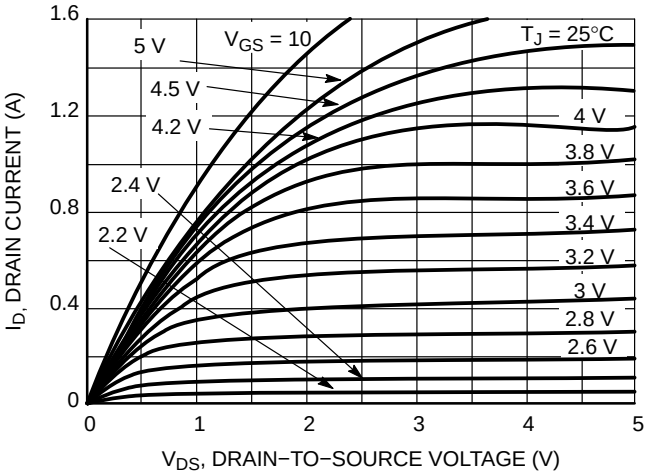


Figure 1. On−Region Characteristics

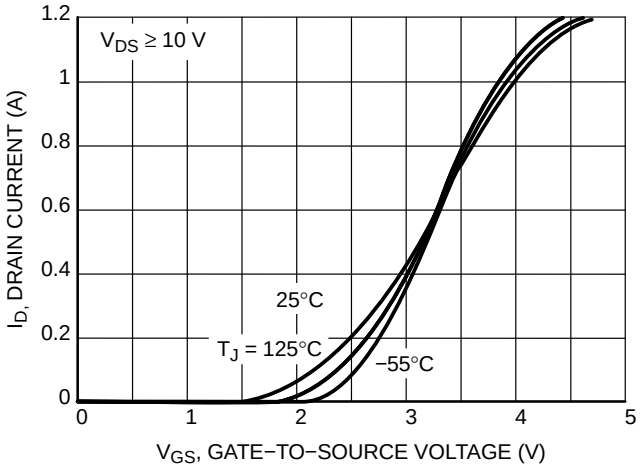


Figure 2. Transfer Characteristics

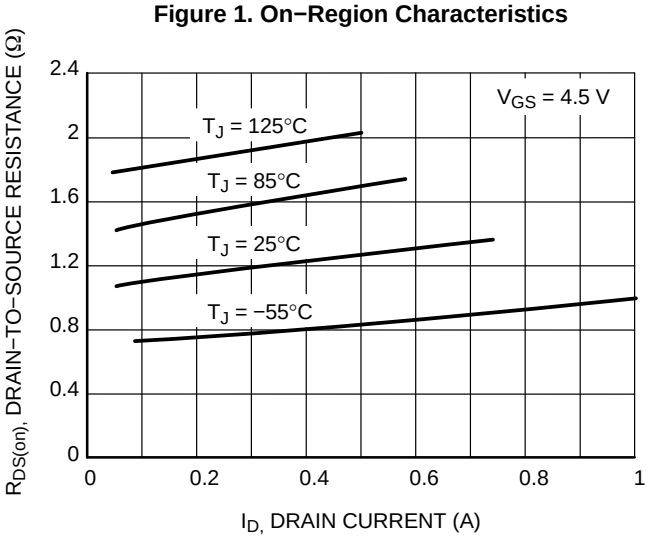


Figure 3. On−Resistance vs. Drain Current and Temperature

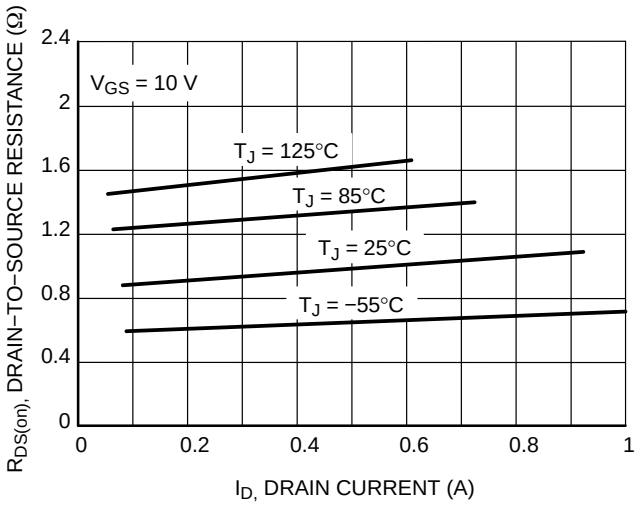


Figure 4. On−Resistance vs. Drain Current and Temperature

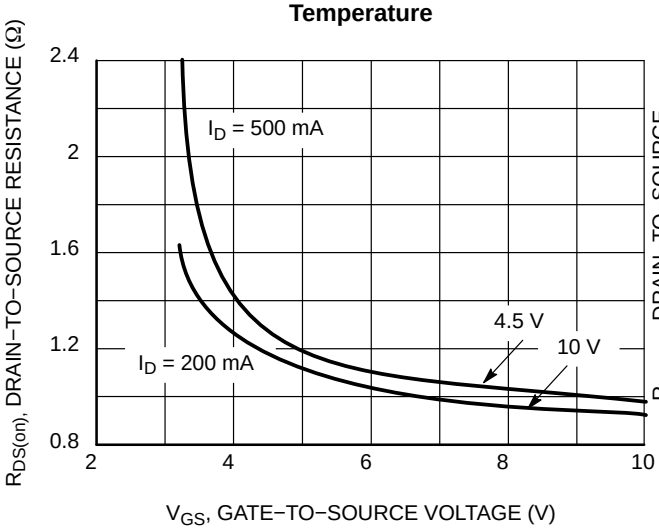


Figure 5. On−Resistance versus Gate−to−Source Voltage

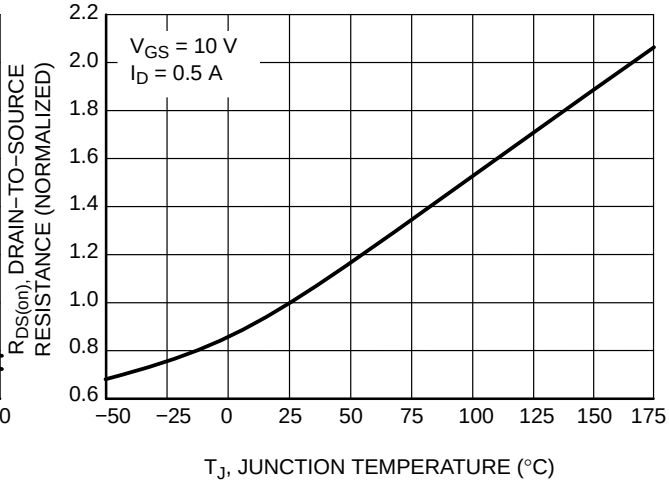


Figure 6. On−Resistance Variation with Temperature

TYPICAL PERFORMANCE CURVES

(T_J = 25°C unless otherwise noted)

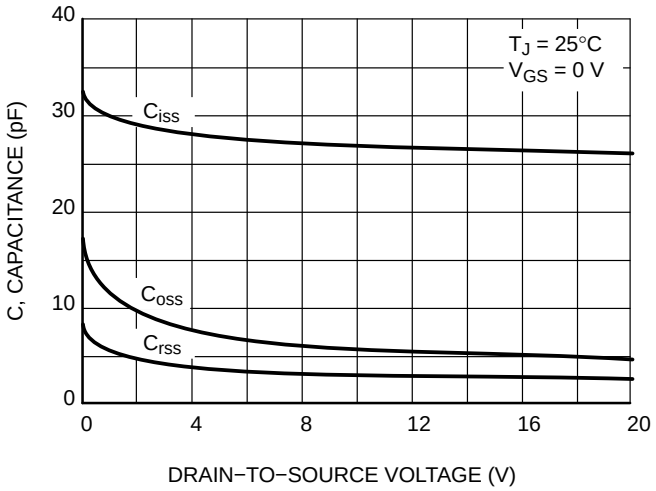


Figure 7. Capacitance Variation

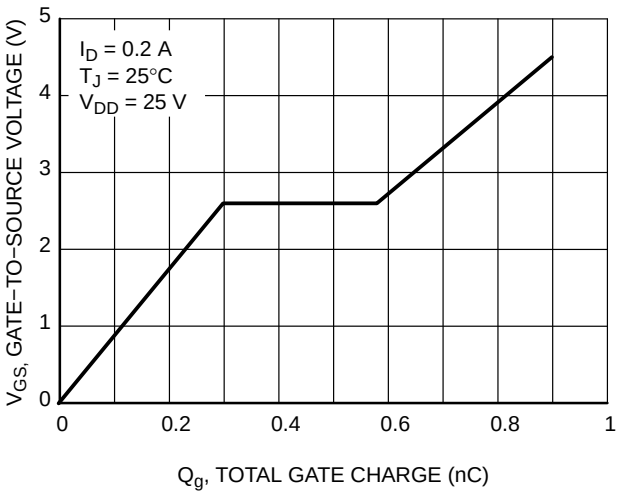


Figure 8. Gate−to−Source and Drain−to−Source Voltage vs. Total Charge

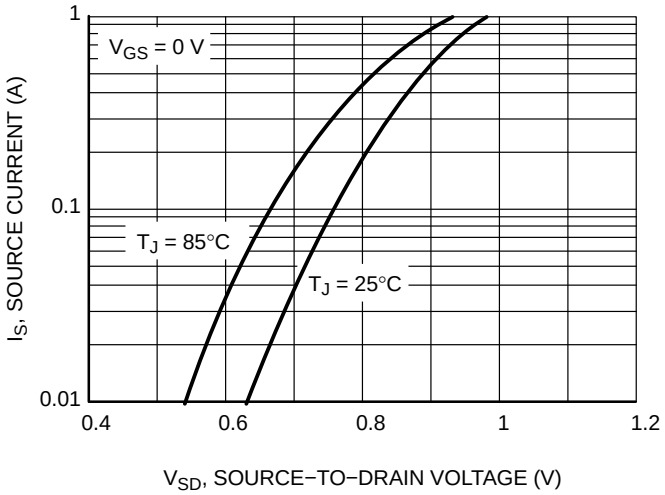
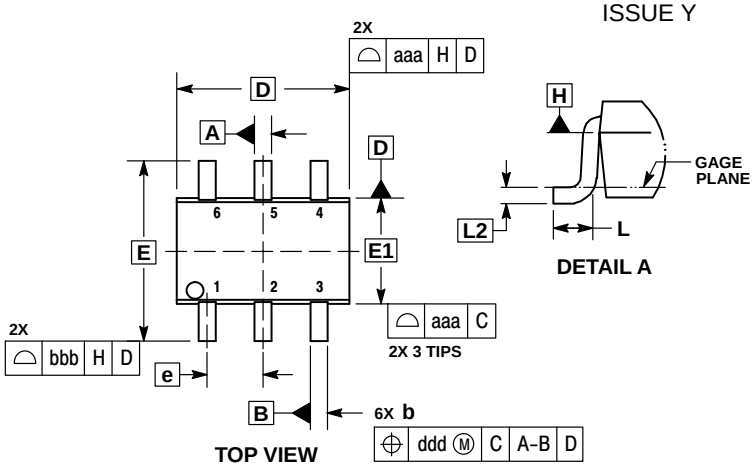
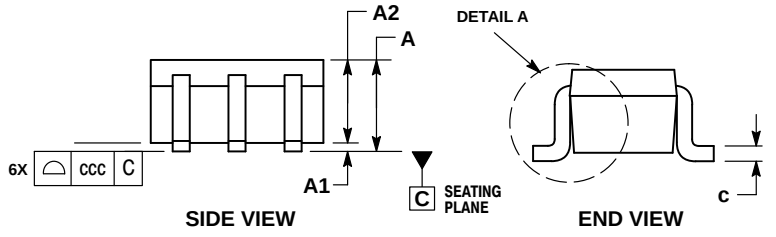


Figure 9. Diode Forward Voltage vs. Current

PACKAGE DIMENSIONS

SC−88/SC70−6/SOT−363
CASE 419B−02
ISSUE Y



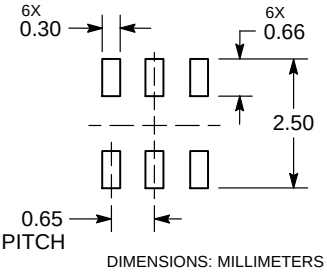


NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
5. DATUMS A AND B ARE DETERMINED AT DATUM H.
6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

	MILLIMETERS			INCHES		
DIM	**MIN**	**NOM**	**MAX**	**MIN**	**NOM**	**MAX**
A	−−−	−−−	1.10	−−−	−−−	0.043
A1	0.00	−−−	0.10	0.000	−−−	0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.15	0.20	0.25	0.006	0.008	0.010
C	0.08	0.15	0.22	0.003	0.006	0.009
D	1.80	2.00	2.20	0.070	0.078	0.086
E	2.00	2.10	2.20	0.078	0.082	0.086
E1	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.26	0.36	0.46	0.010	0.014	0.018
L2	0.15 BSC			0.006 BSC		
aaa	0.15			0.006		
bbb	0.30			0.012		
ccc	0.10			0.004		
ddd	0.10			0.004		

STYLE 26:
PIN 1. SOURCE 1
2. GATE 1
3. DRAIN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
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